

FIG. 2

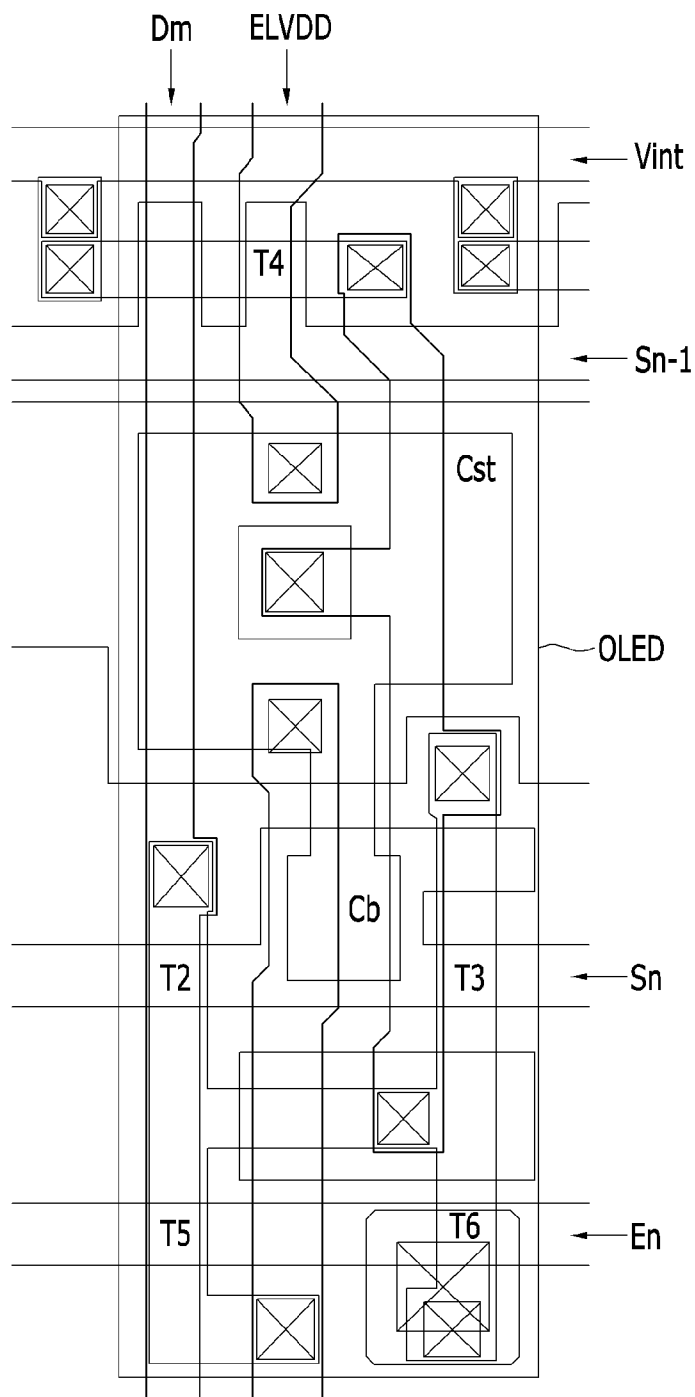


FIG. 3

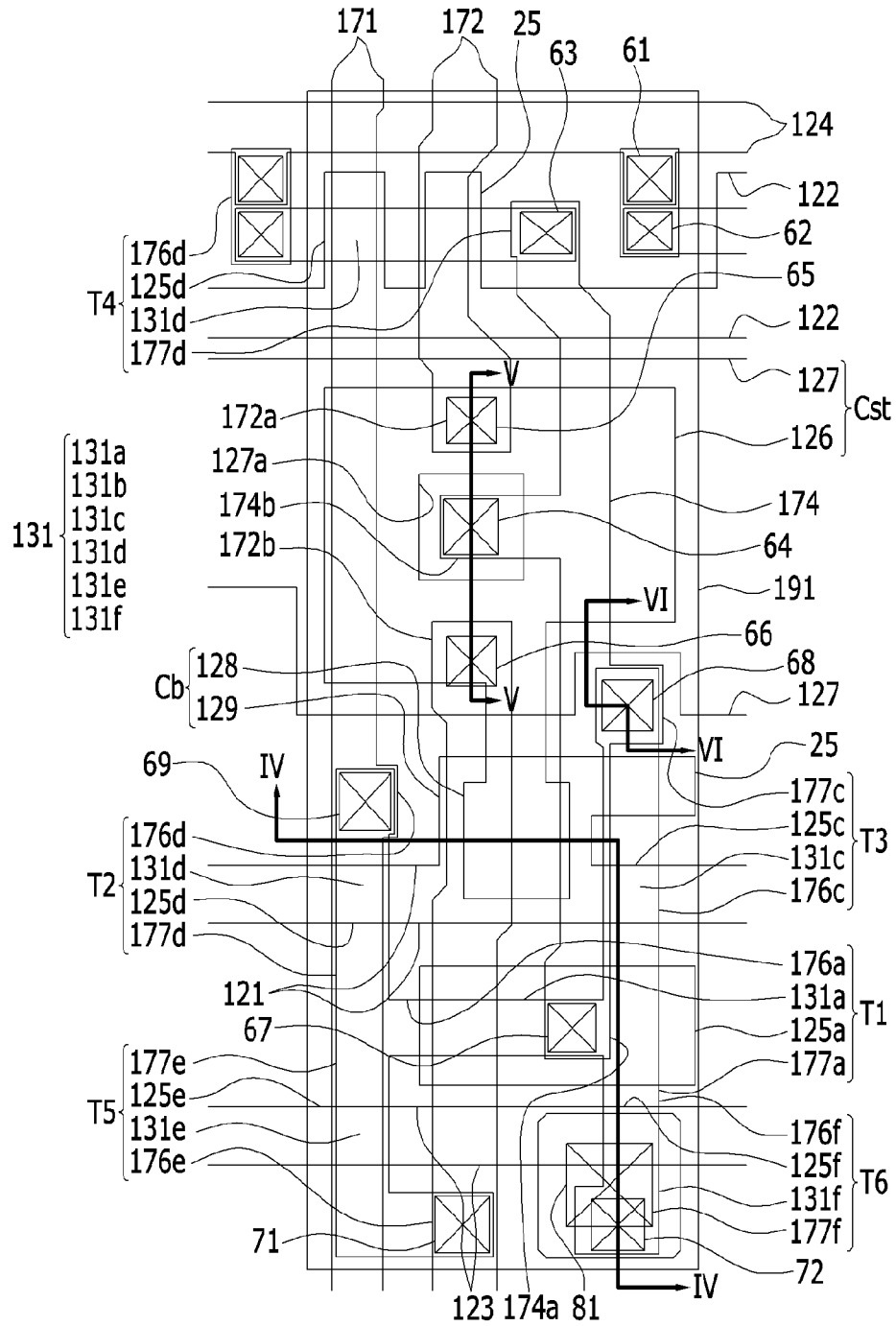


FIG. 4

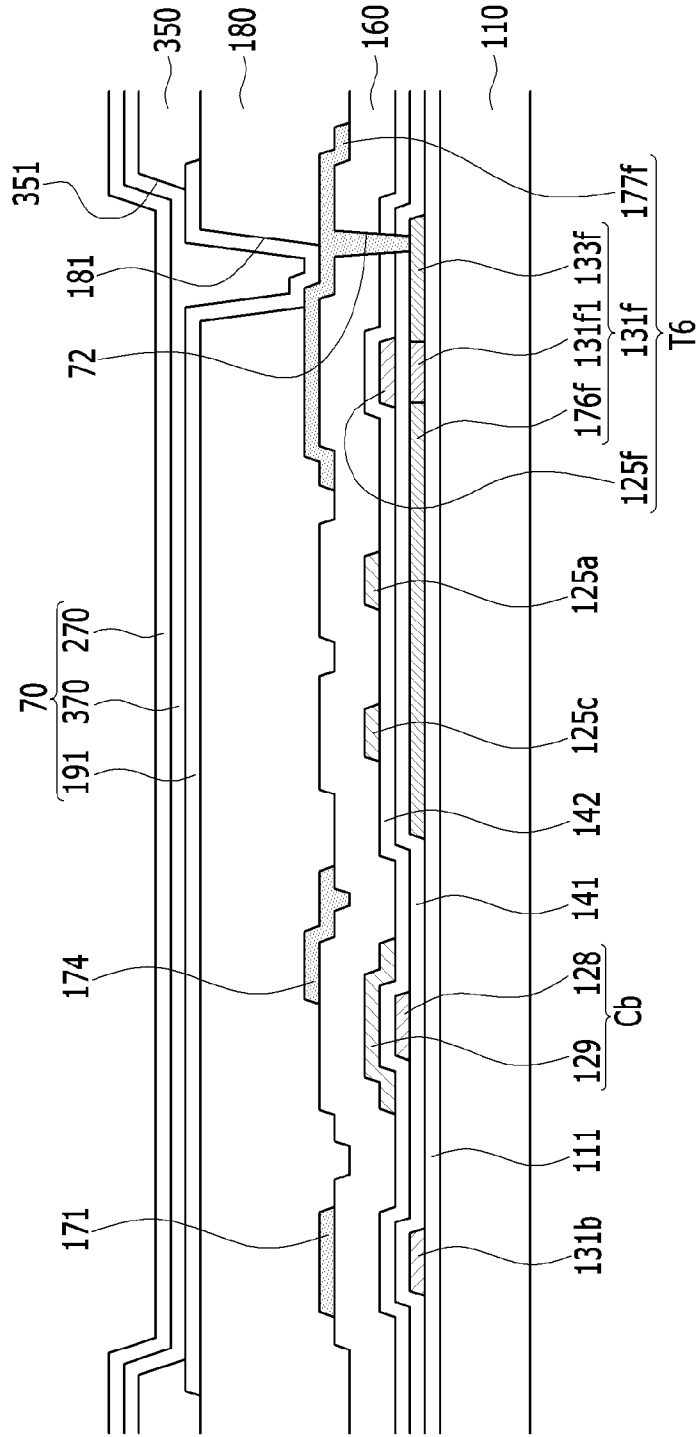


FIG. 5

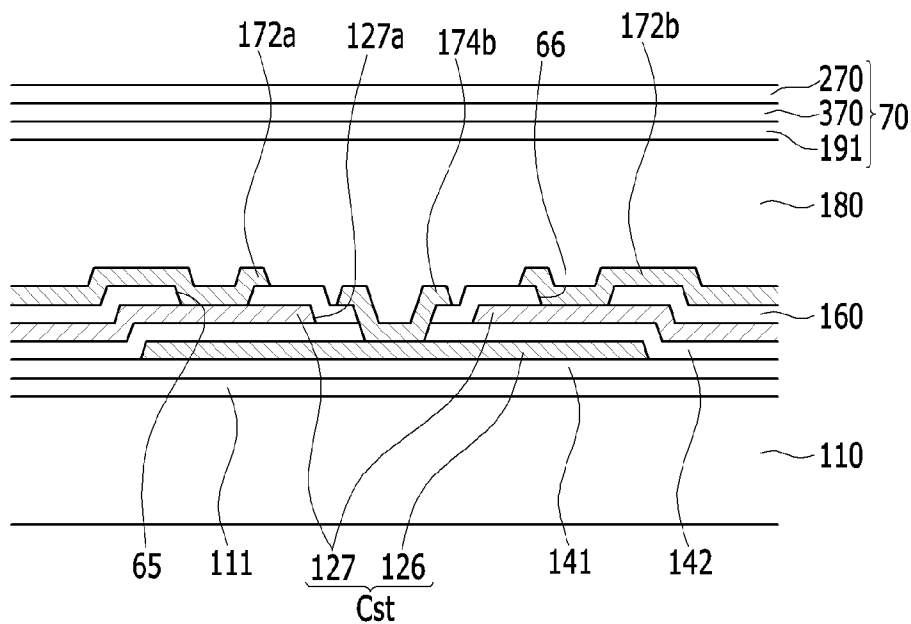
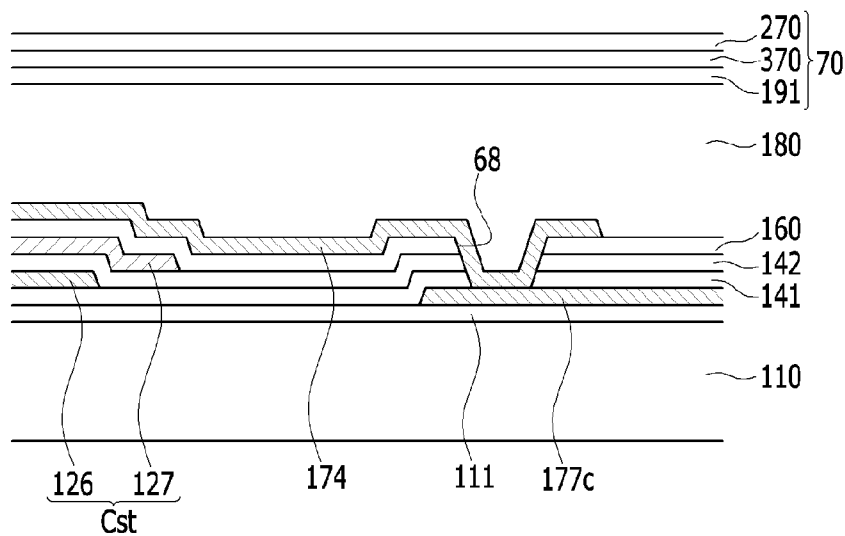


FIG. 6



**ORGANIC LIGHT EMITTING DIODE
DISPLAY**

**CROSS-REFERENCE TO RELATED
APPLICATIONS**

[0001] This application claims priority to and the benefit of Korean Patent Application No. 10-2012-0111339 filed in the Korean Intellectual Property Office on Oct. 8, 2012, the entire contents of which are incorporated herein by reference.

BACKGROUND

[0002] 1. Field

[0003] The described technology relates generally to an organic light emitting diode (OLED) display.

[0004] 2. Description of the Related Technology

[0005] An OLED display includes two electrodes and an organic emission layer that is positioned therebetween. Electrons that are injected from one electrode and holes that are injected from the other electrode form excitons by coupling in the organic emission layer, and the excitons emit light while discharging energy.

[0006] Such an OLED display includes a plurality of pixels including an OLED, which is a self-luminance element. At each pixel, a plurality of thin film transistors (TFT) and at least one capacitor for driving the OLED are formed. The plurality of TFTs include a switching TFT and a driving TFT.

[0007] The capacitor includes a storage capacitor that stores a data signal and a boosting capacitor that performs a boosting operation according to a voltage change of a signal line in order to more accurately express grayscales. Luminance of a pixel including the storage capacitor and the boosting capacitor changes according to a capacitance ratio of the two capacitors.

[0008] The above information disclosed in this Background section is only for enhancement of understanding of the background of the described technology and therefore it may contain information that does not form the prior art that is already known in this country to a person of ordinary skill in the art.

SUMMARY OF CERTAIN INVENTIVE ASPECTS

[0009] The described technology has been made in an effort to provide an OLED display having advantages of being capable of preventing a stain due to a capacitance deviation between a storage capacitor and a boosting capacitor that are provided in a plurality of pixels.

[0010] One embodiment provides an OLED display including: a substrate; a scan line formed over the substrate and configured to transfer a scan signal; a data line and a driving voltage line that intersect the scan line and that are configured to transfer a data signal and a driving voltage, respectively; a switching thin film transistor (TFT) connected to the scan line and the data line; a driving TFT connected to the switching TFT and the driving voltage line, the driving TFT including a driving gate electrode; an OLED that is connected to the driving TFT; a storage capacitor connected between the driving voltage line and the driving gate electrode; and a boosting capacitor connected to the storage capacitor, wherein the storage capacitor has at least one capacitor opening.

[0011] The driving TFT may include a driving semiconductor layer formed over the substrate; the driving gate electrode formed on a first gate insulating layer and a second gate

insulating layer that sequentially cover the driving semiconductor layer, the driving gate electrode overlapped with the driving semiconductor layer.

[0012] The storage capacitor may include a first storage capacitor plate formed over the first gate insulating layer; a second gate insulating layer covering the first storage capacitor plate; and a second storage capacitor plate formed over the second gate insulating layer and overlapped with the first storage capacitor plate.

[0013] The capacitor opening may be formed in the second storage capacitor plate.

[0014] The OLED may further include an interlayer insulating layer covering the second storage capacitor plate, wherein the driving gate electrode is connected to the first storage capacitor plate through a contact hole positioned within the capacitor opening and formed in the interlayer insulating layer and the second gate insulating layer.

[0015] The driving voltage line may be formed over the interlayer insulating layer and spaced apart from the capacitor opening.

[0016] A first side separation terminal and a second side separation terminal of the driving voltage line may be connected to the second storage capacitor plate through a first side contact hole and a second side contact hole, respectively, that are formed in the interlayer insulating layer.

[0017] The OLED display may further include a connection member formed in the same layer, and configured to be parallel to the driving voltage line, and further configured to connect the driving gate electrode and the first storage capacitor plate.

[0018] A first end of the connection member may be connected to the driving gate electrode through a contact hole formed in the interlayer insulating layer, and a first intermediate protruding portion of the connection member may be connected to the first storage capacitor plate through a contact hole formed in the interlayer insulating layer and the second gate insulating layer.

[0019] The OLED display may further include an initialization TFT configured to be turned on according to a previous scan signal received through a previous scan line and further configured to transfer an initialization voltage to a driving gate electrode of the driving TFT, wherein a second end of the connection member may be connected to an initialization semiconductor layer of the initialization TFT through a contact hole formed in the interlayer insulating layer, the second gate insulating layer, and the first gate insulating layer.

[0020] The OLED display may further include a compensating TFT configured to compensate a threshold voltage of the driving TFT and connected to the driving TFT, wherein a second intermediate protruding portion of the connection member may be connected to a compensation semiconductor layer of the compensation TFT through a contact hole formed in the interlayer insulating layer, the second gate insulating layer, and the first gate insulating layer.

[0021] The boosting capacitor may include a first boosting capacitor plate extended from the first storage capacitor and a second boosting capacitor plate overlapped with the first boosting capacitor plate and protruded from the scan line.

[0022] The scan line and the driving gate electrode may be formed co-planar with the second storage capacitor plate.

[0023] The previous scan line may be formed co-planar with the first storage capacitor plate.

[0024] The first storage capacitor plate may be formed co-planar with the first boosting capacitor plate, and the second storage capacitor plate may be formed co-planar with the second boosting capacitor plate.

[0025] According to one embodiment, because a storage capacitor has at least one capacitor opening, a capacitance ratio of a storage capacitor and a boosting capacitor can be uniformly sustained even in an over-etching phenomenon. Therefore, because a deviation does not occur in a capacitance ratio between a storage capacitor and a boosting capacitor that are provided in a plurality of pixels, a stain can be prevented from occurring.

[0026] Further, by separating a driving voltage line from a position corresponding to a capacitor opening, connecting one side separation terminal and the other side separation terminal of the driving voltage line to the second storage capacitor plate through a first side contact hole and a second side contact hole, respectively, that are formed in an interlayer insulating layer, connecting a first storage capacitor plate and a driving gate electrode that are exposed through a capacitor opening using a connection member, a capacitor opening can be formed within the storage capacitor.

BRIEF DESCRIPTION OF THE DRAWINGS

[0027] FIG. 1 is an equivalent circuit diagram of one pixel of an OLED display according to one embodiment.

[0028] FIG. 2 is a diagram illustrating a position of a plurality of TFTs and a capacitor at one pixel of an OLED display according to one embodiment.

[0029] FIG. 3 is a specific layout view of one pixel of an OLED display according to one embodiment.

[0030] FIG. 4 is a cross-sectional view illustrating an OLED display taken along line IV-IV of FIG. 3.

[0031] FIG. 5 is a cross-sectional view illustrating an OLED display taken along line V-V of FIG. 3.

[0032] FIG. 6 is a cross-sectional view illustrating an OLED display taken along line VI-VI of FIG. 3.

DETAILED DESCRIPTION OF CERTAIN INVENTIVE EMBODIMENTS

[0033] The present invention will be described more fully hereinafter with reference to the accompanying drawings, in which certain embodiments of the invention are shown. As those skilled in the art would realize, the described embodiments may be modified in various ways, without departing from the spirit or scope of the present invention.

[0034] The drawings and description are to be regarded as illustrative in nature and not restrictive. Like reference numerals generally designate like elements throughout the specification.

[0035] Further, in the drawings, a size and thickness of each element are represented for better understanding and ease of description, and the present invention is not limited thereto.

[0036] In the drawings, the thickness of layers, films, panels, regions, etc., may be exaggerated for clarity. In the drawings, for better understanding and ease of description, thicknesses of some layers and areas may be excessively displayed. It will be understood that when an element such as a layer, film, region, or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present.

[0037] In addition, unless explicitly described to the contrary, the word "comprise" and variations such as "com-

prises" or "comprising", will be understood to imply the inclusion of stated elements but not the exclusion of any other elements. Further, in the specification, an upper part of a target portion indicates an upper part or a lower part of the target portion, and the target portion is not always positioned at the upper side based on a gravity direction.

[0038] Further, in the attached drawings, an active matrix (AM) OLED display of a 6Tr 2Cap structure having 6 TFTs and two capacitors at one pixel is illustrated, but the present invention is not limited thereto. Therefore, the OLED display may have a plurality of TFTs and at least one capacitor at one pixel, and as a separate wire is further formed or an existing wire is omitted, the OLED display may be formed to have various structures. Here, a pixel is a minimum unit that displays an image, and the OLED display displays an image through a plurality of pixels.

[0039] Hereinafter, an OLED display according to one embodiment will be described in detail with reference to FIGS. 1 to 5.

[0040] In order to express uniform luminance, a capacitance ratio of a storage capacitor and a boosting capacitor should be uniformly sustained between a plurality of pixels. When a deviation occurs in the capacitance ratio, a stain occurs by a luminance deviation and a color deviation. Particularly, because an area of the boosting capacitor is smaller than that of the storage capacitor, a micro over-etching phenomenon, i.e., a skew in a production process has a large influence on an area of the boosting capacitor and thus a stain may occur at a pixel.

[0041] FIG. 1 is an equivalent circuit diagram of one pixel of an OLED display according to one embodiment.

[0042] As shown in FIG. 1, one pixel of an OLED display according to an embodiment includes a plurality of signal lines 121, 122, 123, 124, 171, and 172, a plurality of TFTs T1, T2, T3, T4, T5, and T6 that are connected to the plurality of signal lines, capacitors Cst and Cb, and an OLED.

[0043] The TFTs includes a driving TFT T1, a switching TFT T2, a compensation TFT T3, and an initialization TFT T4, an operation control TFT T5, and a light emission control TFT T6, and the capacitors include a storage capacitor Cst and a boosting capacitor Cb.

[0044] The signal lines includes a scan line 121 that transfers a scan signal Sn to the switching TFT T2 and the boosting capacitor Cb, a previous scan line 122 that transfers a previous scan signal Sn-1 to the initialization TFT T4, a light emission control line 123 that transfers a light emission control signal En to the operation control TFT T5 and the light emission control TFT T6, a data line 171 that intersects the scan line 121 and that transfers a data signal Dm, a driving voltage line 172 that transfers a driving voltage ELVDD and that is formed substantially parallel to the data line 171, and an initialization voltage line 124 that transfers an initialization voltage Vint that initializes the driving TFT T1.

[0045] A gate electrode G1 of the driving TFT T1 is connected to one end Cst1 of a storage capacitor Cst. A source electrode S1 of the driving TFT T1 is connected to the driving voltage line 172 via the operation control TFT T5. A drain electrode D1 of the driving TFT T1 is electrically connected to an anode of the OLED via the light emission control TFT T6. The driving TFT T1 receives a data signal Dm according to a switching operation of the switching TFT T2 and supplies a driving current Id to the OLED.

[0046] A gate electrode G2 of the switching TFT T2 is connected to the scan line 121, the other end Cb2 of the

boosting capacitor Cb, and a gate electrode G3 of the compensation TFT T3. A source electrode S2 of the switching TFT T2 is connected to the data line 171. A drain electrode D2 of the switching TFT T2 is connected to the driving voltage line 172 via the operation control TFT T5 while being connected to a source electrode S1 of the driving TFT T1. The switching TFT T2 is turned on according to a scan signal Sn received through the scan line 121, and performs a switching operation that transfers a data signal Dm to the source electrode S1 of the driving TFT T1.

[0047] A gate electrode G3 of the compensation TFT T3 is connected to the scan line 121, the gate electrode G2 of the switching TFT T2, the other end Cb2 of the boosting capacitor Cb. A source electrode S3 of the compensation TFT T3 is connected to an anode of the OLED via the light emission control TFT T6 while being connected to a drain electrode D1 of the driving TFT T1. A drain electrode D3 of the compensation TFT T3 is connected to one end Cst1 of the capacitor Cst, one end Cb1 of the boosting capacitor Cb, a gate electrode G1 of the driving TFT T1, and a drain electrode D4 of the initialization TFT T4. The compensation TFT T3 is turned on according to a scan signal Sn received through the scan line 121 to connect a gate electrode G1 and a drain electrode D1 of the driving TFT T1, and to perform a diode-connection of the driving TFT T1.

[0048] A gate electrode G4 of the initialization TFT T4 is connected to the previous scan line 122. A source electrode S4 of the initialization TFT T4 is connected to the initialization voltage line 124. A drain electrode D4 of the initialization TFT T4 is connected to one end Cb1 of the boosting capacitor Cb, one end Cst1 of the storage capacitor Cst, a drain electrode D3 of the compensation TFT T3, and a gate electrode G1 of the driving TFT T1. The initialization TFT T4 is turned on according to the previous scan signal Sn-1 received through the previous scan line 122, transfers an initialization voltage Vint to the gate electrode G1 of the driving TFT T1, and performs an initialization operation that initializes a voltage of the gate electrode G1 of the driving TFT T1.

[0049] A gate electrode G5 of the operation control TFT T5 is connected to the light emitting control line 123. A source electrode S5 of the operation control TFT T5 is connected to the driving voltage line 172. A drain electrode D5 of the operation control TFT T5 is connected to the source electrode S1 of the driving TFT T1 and the drain electrode S2 of the switching TFT T2.

[0050] A gate electrode G6 of the light emitting control TFT T6 is connected to the light emitting control line 123. A source electrode S6 of the light emitting control TFT T6 is connected to a drain electrode D1 of the driving TFT T1 and a source electrode S3 of the compensation TFT T3. A drain electrode D6 of the light emitting control TFT T6 is electrically connected to an anode of the OLED. The operation control TFT T5 and the light emission control TFT T6 are turned on according to the light emission control signal En received through the light emission control line 123 and thus a driving voltage ELVDD is transferred to the OLED to enable a driving current Id to flow to the OLED.

[0051] The other end Cst2 of the storage capacitor Cst is connected to the driving voltage line 172, and a cathode of the OLED is connected to a common voltage ELVSS. Accordingly, the OLED receives a driving current Id from the driving TFT T1 and emits light, thereby displaying an image.

[0052] Hereinafter, a specific operation process of one pixel of an OLED display according to an embodiment will be described in detail.

[0053] First, for an initialization period, the previous scan signal Sn-1 of a low level is supplied through the previous scan line 122. Therefore, the initialization TFT T4 is turned on to correspond to the previous scan signal Sn-1 of a low level, the initialization voltage Vint is connected from the initialization voltage line 124 to the gate electrode G1 of the driving TFT T1 through the initialization TFT T4, and the driving TFT T1 is initialized by the initialization voltage Vint.

[0054] Thereafter, for a data programming period, a scan signal Sn of a low level is supplied through the scan line 121. Therefore, the switching TFT T2 and the compensation TFT T3 are turned on to correspond to the scan signal Sn of a low level.

[0055] In this case, the driving TFT T1 is diode-connected by the turned-on compensation TFT T3 and is biased in a forward direction.

[0056] Therefore, a compensation voltage (Dm+Vth) (where Vth is a negative (-) value) that is reduced by a threshold voltage Vth of the driving TFT T1 from a data signal Dm that is supplied from the data line 171 is applied to the gate electrode G1 of the driving TFT T1.

[0057] The driving voltage ELVDD and a compensation voltage Dm+Vth are applied to both ends of the storage capacitor Cst, and charges corresponding to a voltage difference between the two ends of the capacitor are stored at the storage capacitor Cst.

[0058] Thereafter, while the supply of the scan signal Sn is stopped, when a voltage level of the scan signal Sn is changed to a high level, a voltage that is applied to the gate electrode G1 of the driving TFT T1 by a coupling operation of the boosting capacitor Cb is changed to correspond to a voltage change width of the scan signal Sn. In this case, because a voltage that is applied to the gate electrode G1 of the driving TFT T1 is changed by charge sharing between the storage capacitor Cst and the boosting capacitor Cb, a voltage change amount that is applied to the driving gate electrode G1 is changed proportional to a charge sharing value between the storage capacitor Cst and the boosting capacitor Cb together with a voltage change width of the scan signal Sn.

[0059] Thereafter, for a light emitting period, a light emission control signal En that is supplied from the light emission control line 123 is changed from a high level to a low level. Therefore, for a light emitting period, the operation control TFT T5 and the light emission control TFT T6 are turned on by the light emission control signal En of a low level.

[0060] Therefore, a driving current Id is generated according to a voltage difference between a voltage of the gate electrode G1 of the driving TFT T1 and the driving voltage ELVDD, and the driving current Id is supplied to the OLED through the light emission control TFT T6. For a light emitting period, a gate-source voltage Vgs of the driving TFT T1 is sustained to 'Dm+Vth-ELVDD' by the storage capacitor Cst, and a driving current Id is proportional to the square '(Dm-ELVDD)²' of a value that subtracts a threshold voltage Vth from a gate-source voltage Vgs according to a current-voltage relationship of the driving TFT T1. Therefore, the driving current Id is determined regardless of the threshold voltage Vth of the driving TFT T1.

[0061] Hereinafter, a detailed structure of a pixel of the OLED display that is shown in FIG. 1 will be described in detail with reference to FIGS. 2 to 6.

[0062] FIG. 2 is a diagram illustrating a position of a plurality of TFTs and a capacitor at one pixel of an OLED display according to an embodiment, FIG. 3 is a specific layout view of one pixel of an OLED display according to an embodiment, FIG. 4 is a cross-sectional view illustrating an OLED display taken along line IV-IV of FIG. 3, FIG. 5 is a cross-sectional view illustrating an OLED display taken along line V-V of FIG. 3, and FIG. 6 is a cross-sectional view illustrating an OLED display taken along line VI-VI of FIG. 3.

[0063] As shown in FIGS. 2 to 6, a pixel of the OLED display according to an embodiment includes a scan line 121, a previous scan line 122, a light emission control line 123, and an initialization voltage line 124 that apply a scan signal S_n , a previous scan signal S_{n-1} , a light emission control signal E_n , and an initialization voltage V_{int} , respectively to the pixel, and that are formed in a row direction. The pixel of the OLED display also includes a data line 171 and a driving voltage line 172 that intersect all of the scan line 121, the previous scan line 122, the light emission control line 123, and the initialization voltage line 124, and that apply a data signal D_m and a driving voltage $ELVDD$, respectively, to the pixel.

[0064] Further, at the pixel, the driving TFT T1, the switching TFT T2, the compensation TFT T3, the initialization TFT T4, the operation control TFT T5, the light emission control TFT T6, the storage capacitor C_{st} , the boosting capacitor C_b , and an OLED 70 are formed.

[0065] The driving TFT T1, the switching TFT T2, the compensation TFT T3, the initialization TFT T4, the operation control TFT T5, and the light emission control TFT T6 are formed along a semiconductor layer 131, and the semiconductor layer 131 is bent in various shapes. Such a semiconductor layer 131 is made of polysilicon and includes a channel area in which impurities are not doped and a source area and a drain area that are doped with impurities at both sides of the channel area. Such impurities change according to a kind of a TFT and may be an N type impurity or a P type impurity. The semiconductor layer includes a driving semiconductor layer 131a that is formed in the driving TFT T1, a switching semiconductor layer 131b that is formed in the switching TFT T2, a compensation semiconductor layer 131c that is formed in the compensation TFT T3, an initialization semiconductor layer 131d that is formed in the initialization TFT T4, and an operation control semiconductor layer 131e and a light emission control semiconductor layer 131f that are formed in the operation control TFT T5 and the light emission control TFT T6, respectively.

[0066] The driving TFT T1 includes the driving semiconductor layer 131a, a driving gate electrode 125a, a driving source electrode 176a, and a driving drain electrode 177a. The driving source electrode 176a corresponds to a driving source area 176a that is doped with impurities in the driving semiconductor layer 131a, and the driving drain electrode 177a corresponds to a driving drain area 177a that is doped with impurities in the driving semiconductor layer 131a. The driving gate electrode 125a is overlapped with the driving semiconductor layer 131a and has a rectangular shape.

[0067] The driving gate electrode 125a is formed in the same layer and with the same material as that of the scan line 121, the initialization voltage line 124, a switching gate electrode 125b, a compensation gate electrode 125c, a second storage capacitor plate 127, and a second boosting capacitor plate 129.

[0068] The switching TFT T2 includes a switching semiconductor layer 131b, the switching gate electrode 125b, a switching source electrode 176b, and a switching drain electrode 177b. The switching drain electrode 177b corresponds to a switching drain area 177b that is doped with impurities in the switching semiconductor layer 131b.

[0069] The compensation TFT T3 includes a compensation semiconductor layer 131c, a compensation gate electrode 125c, a compensation source electrode 176c, and a compensation drain electrode 177c, and the compensation source electrode 176c corresponds to a compensation source area that is doped with impurities in the compensation semiconductor layer 131c. The compensation gate electrode 125c forms a separate dual gate electrode 25, thereby preventing a leakage current.

[0070] The initialization TFT T4 includes an initialization semiconductor layer 131d, an initialization gate electrode 125d, an initialization source electrode 176d, and an initialization drain electrode 177d. One end of the initialization source electrode 176d is connected to the initialization voltage line 124 through a contact hole 61 that is formed in the interlayer insulating layer 160, and the other end of the initialization source electrode 176d is connected to the initialization semiconductor layer 131d through a contact hole 62 that is continuously formed in the first gate insulating layer 141, the second gate insulating layer 142, and the interlayer insulating layer 160. The initialization drain electrode 177d is the other end of a connection member 174 and is connected to the initialization semiconductor layer 131d through the contact hole 63 that is continuously formed in the first gate insulating layer 141, the second gate insulating layer 142, and the interlayer insulating layer 160.

[0071] The operation control TFT T5 includes an operation control semiconductor layer 131e, an operation control gate electrode 125e, an operation control source electrode 176e, and an operation control drain electrode 177e. The operation control source electrode 176e is a portion of the driving voltage line 172, is connected to an operation control source area through a contact hole 71. The operation control drain electrode 177e corresponds to an operation control drain area 177e that is doped with impurities in the operation control semiconductor layer 131e.

[0072] The light emission control TFT T6 includes a light emission control semiconductor layer 131f, a light emission control gate electrode 125f, a light emission control source electrode 176f, and a light emission control drain electrode 177f. The light emission control source electrode 176f corresponds to a light emission control source area 176f that is doped with impurities in the light emission control semiconductor layer 131f.

[0073] One end of the driving semiconductor layer 131a of the driving TFT T1 is connected to the switching semiconductor layer 131b and the operation control semiconductor layer 131e, and the other end of the driving semiconductor layer 131a is connected to the compensation semiconductor layer 131c and the light emission control semiconductor layer 131f. Therefore, the driving source electrode 176a is connected to the switching drain electrode 177b and the operation control drain electrode 177e, and the driving drain electrode 177a is connected to the compensation source electrode 176c and the light emission control source electrode 176f.

[0074] As shown in FIG. 5, the storage capacitor C_{st} includes a first storage capacitor plate 126 and a second storage capacitor plate 127 that together interpose the second

gate insulating layer **142** therebetween. The second gate insulating layer **142** is a dielectric material, and storage capacitance is determined by charges that are stored at the storage capacitor **Cst** and a voltage between both capacitor plates **126** and **127**.

[0075] The first storage capacitor plate **126** is formed in the same layer and with the same material as that of the previous scan line **122**, the light emission control line **123**, the operation control gate electrode **125e**, the light emission control gate electrode **125f**, and the first boosting capacitor plate **128**. The second storage capacitor plate **127** is formed in the same layer and with the same material as that of the scan line **121**, the initialization voltage line **124**, the driving gate electrode **125a**, the switching gate electrode **125b**, the compensation gate electrode **125c**, and the second boosting capacitor plate **129**. The first storage capacitor plate **126** and the second storage capacitor plate **127** are formed with a gate wire including at least one metal of aluminum (Al), chromium (Cr), molybdenum (Mo), titanium (Ti), tantalum (Ta), Al—Ni—La alloy, and Al—Nd alloy. Therefore, storage capacitance can be improved, compared with a structure that forms any one capacitor plate of the storage capacitor **Cst** with a semiconductor layer.

[0076] The storage capacitor **Cst** has at least one capacitor opening **126a**, and specifically, a capacitor opening **126a** is formed in the second storage capacitor plate **127**. Therefore, because the inside of the storage capacitor **Cst** is over-etched together with the outside of the storage capacitor **Cst** by an over-etching phenomenon occurring in a production process, a skew area of the storage capacitor **Cst** is larger than that of the boosting capacitor **Cb**, and thus a capacitance ratio of the storage capacitor **Cst** and the boosting capacitor **Cb** may be uniformly sustained even in an over-etching phenomenon. Therefore, because a deviation does not occur at a capacitance ratio between the boosting capacitor **Cb** and the storage capacitor **Cst**, by minimizing a voltage deviation of the driving gate electrode **125a** of the driving TFT **T1**, a stain is prevented from occurring.

[0077] The driving voltage line **172** passing through to overlap with the storage capacitor **Cst** is separated at a position at which the capacitor opening **126a** is formed. The driving voltage line **172** includes one side separation terminal **172a** that is positioned at one side based on the capacitor opening **126a** and the other side separation terminal **172b** that is positioned at the other side based on the capacitor opening **126a**. One side separation terminal **172a** and the other side separation terminal **172b** of the driving voltage line **172** are connected to the second storage capacitor plate **127** through one side contact hole **65** and the other side contact hole **66**, respectively, that are formed in the interlayer insulating layer **160**.

[0078] The connection member **174** is formed in the same layer to be parallel to the driving voltage line **172**. The connection member **174** connects the driving gate electrode **125a** and the first storage capacitor plate **126**. One end **174a** of the connection member **174** is connected to the driving gate electrode **125a** through the contact hole **67** that is formed in the interlayer insulating layer **160**, and a first intermediate protruding portion **174b** of the connection member **174** is connected to the first storage capacitor plate **126** through a contact hole **64** that is formed in the interlayer insulating layer **160** and the second gate insulating layer **142** that is positioned at the inside of the capacitor opening **126a**.

[0079] The other end **177d** of the connection member **174** corresponds to an initialization drain electrode **177d** of the initialization TFT **T4** and is connected to the initialization semiconductor layer **131d** of the initialization TFT **T4** through a contact hole **63** that is continuously formed in the first gate insulating layer **141**, the second gate insulating layer **142**, and the interlayer insulating layer **160**. Further, the second intermediate protruding portion **177c** of the connection member **174** corresponds to the compensation drain electrode **177c** of the compensation TFT **T3** and is connected to the compensation semiconductor layer **131c** of the compensation TFT **T3** through the contact hole **68** that is continuously formed in the first gate insulating layer **141**, the second gate insulating layer **142**, and the interlayer insulating layer **160**.

[0080] Therefore, the first storage capacitor plate **126** of the storage capacitor **Cst** is connected to the compensation semiconductor layer **125c** and an initialization semiconductor layer **125d** through the second intermediate protruding portion **177c** and the other end **177d** of the connection member **174** and is connected to the driving gate electrode **125a** through one end **174a** of the connection member **174**. The second storage capacitor plate **127** of the storage capacitor **Cst** is connected to the driving voltage line **172** through one side contact hole **65** and the other side contact hole **66** that is formed in the interlayer insulating layer **160**.

[0081] Therefore, the storage capacitor **Cst** stores storage capacitance corresponding to a difference between a gate voltage of the driving gate electrode **125a** and a driving voltage **ELVDD** that is transferred through the driving voltage line **172**.

[0082] In this way, the driving voltage line **172** is separated from a position corresponding to the capacitor opening **126a**, and one side separation terminal **172a** and the other side separation terminal **172b** of the driving voltage line **172** are connected to the second storage capacitor plate **127** through one side contact hole **65** and the other side contact hole **66**, respectively, that are formed in the interlayer insulating layer **160** and connect the first storage capacitor plate **126** and the driving gate electrode **125a** that are exposed through the capacitor opening **126a** using the connection member **174**, thereby forming the capacitor opening **126a** at the inside of the storage capacitor **Cst**. In this case, an area and the number of the capacitor openings **126a** that is formed in the storage capacitor **Cst** are determined by a capacitance ratio of the boosting capacitor **Cb**.

[0083] The first boosting capacitor plate **128** of the boosting capacitor **Cb** is extended from the first storage capacitor plate **126**, and the second boosting capacitor plate **129** is protruded from the scan line **121**. The first boosting capacitor plate **128** has a hammer shape, and a first boosting capacitor plate **133** includes a handle portion parallel to the driving voltage line **172** and a head portion that is formed in an end portion of the handle portion. The head portion of the first boosting capacitor plate **128** is positioned to overlap at the inside of the second boosting capacitor plate **129**.

[0084] The switching TFT **T2** is used as a switch that selects a pixel to emit light. The switching gate electrode **125b** is connected to the scan line **121**, the switching source electrode **176b** is connected to the data line **171**, and the switching drain electrode **177b** is connected to the driving TFT **T1** and the operation control TFT **T5**. The light emission control drain electrode **177f** of the light emission control TFT **T6** is

directly connected to a pixel electrode **191** of the organic light emitting diode **70** through a contact hole **181** that is formed in a protective layer **180**.

[0085] Hereinafter, a structure of an OLED display according to an embodiment will be described in detail with reference to FIGS. **4** to **6**.

[0086] A structure of a TFT based on the driving TFT **T1**, the switching TFT **T2**, and the light emission control TFT **T6** will be described, and a storage capacitor **Cst** and the connection member **174** will be described. The remaining TFTs **T3**, **T4**, and **T5** have substantially the same stacked structure as that of the driving TFT **T1**, the switching TFT **T2**, and the light emission control TFT **T6** and therefore a detailed description thereof will be omitted.

[0087] A buffer layer **111** is formed on a substrate **110**, and the substrate **110** is formed as an insulation substrate that is formed with glass, quartz, ceramic, and plastic.

[0088] The switching semiconductor layer **131b**, the driving semiconductor layer **131a**, and the light emission control semiconductor layer **131f** are formed on the buffer layer **111**. The switching semiconductor layer **131b** includes a switching source area and a switching drain area opposite to each other with a switching channel area interposed therebetween. The driving semiconductor layer **131a** includes a driving source area and a driving drain area opposite to each other with a driving channel area interposed therebetween. The light emission control TFT **T6** includes a light emission control channel area **131f1**, a light emission control source area **176f**, and a light emission control drain area **133f**.

[0089] The first gate insulating layer **141** that is formed with silicon nitride SiNx or silicon oxide SiO_2 is formed on the switching semiconductor layer **131a**, the driving semiconductor layer **131b**, and the light emission control semiconductor layer **131f**.

[0090] The previous scan line **122** including an initialization gate electrode **125d**, a light emission control line **123** including the operation control gate electrode **125e** and the light emission control gate electrode **125f**, and first gate wires **122**, **123**, **125d**, **125e**, **125f**, **126**, and **128** including the first storage capacitor plate **126**, and the first boosting capacitor plate **128** are formed on the first gate insulating layer **141**.

[0091] A second gate insulating layer **142** is formed on the first gate wires **122**, **123**, **125d**, **125e**, **125f**, **126**, and **128** and the first gate insulating layer **141**. The second gate insulating layer **142** is made of silicon nitride SiNx or silicon oxide SiO_2 .

[0092] On the second gate insulating layer **142**, a scan line **121** including the driving gate electrode **125a**, the switching gate electrode **125b**, and the compensation gate electrode **125c**, the initialization voltage line **124**, and the second gate wires **125a**, **125b**, **125c**, **121**, **124**, **127**, and **129** including the second storage capacitor plate **127** and the second boosting capacitor plate **129** are formed. A storage opening **127a** for connecting the first storage capacitor plate **126** and the first intermediate protruding portion **174b** of the connection member **174** is formed at the inside of the second storage capacitor plate **127**.

[0093] The interlayer insulating layer **160** is formed on the second gate wires **125a**, **125b**, **125c**, **121**, **124**, **127**, and **129** and the second gate insulating layer **142**. The interlayer insulating layer **160** is made of a ceramic-based material such as silicon nitride SiNx or silicon oxide SiO_2 , as in the first gate insulating layer **141** and the second gate insulating layer **142**.

[0094] On the interlayer insulating layer **160**, a data wire including a data line **171** including the switching source electrode **176b**, the connection member **174** including the initialization drain electrode **177d** and the compensation drain electrode **177c**, and the driving voltage line **172** including the light emission control drain electrode **177f** and the driving control source electrode **176e** are formed.

[0095] The light emission control drain electrode **177f** is connected to the light emission control drain area **133f** of the light emission control semiconductor layer **131f** through a contact hole **72** that is formed in the first gate insulating layer **141**, the second gate insulating layer **142**, and the interlayer insulating layer **160**. The first intermediate protruding portion **174b** of the connection member **174** is connected to the first storage capacitor plate **126** through the contact hole **64** that is continuously formed in the second gate insulating layer **142** and the interlayer insulating layer **160**. One side separation terminal **172a** and the other side separation terminal **172b** of the driving voltage line **172** are connected to the second storage capacitor plate **127** through one side contact hole **65** and the other side contact hole **66**, respectively, that are formed in the interlayer insulating layer **160**. The second intermediate protruding portion **177c** of the connection member **174** is connected to the compensation semiconductor layer **125c** of the compensation TFT **T3** through a contact hole **68** that is continuously formed in the first gate insulating layer **141**, the second gate insulating layer **142**, and the interlayer insulating layer **160**.

[0096] The protective layer **180** that covers data wires **171**, **172**, **174**, and **177f** is formed on the interlayer insulating layer **160**, and the pixel electrode **191** is formed on the protective layer **180**. The pixel electrode **191** is connected to the light emission control drain electrode **177f** through the contact hole **181** that is formed in the protective layer **180**.

[0097] A barrier rib **350** is formed on the protective layer **180** and an edge of the pixel electrode **191**, and the barrier rib **350** has a barrier rib opening **351** that exposes the pixel electrode **191**. The barrier rib **350** may be made of a resin such as a polyacrylates resin and a polyimides resin or a silica-based inorganic material.

[0098] An organic emission layer **370** is formed on the pixel electrode **191** that is exposed by the barrier rib opening **351**, and a common electrode **270** is formed on the organic emission layer **370**. In this way, the OLED **70** including the pixel electrode **191**, the organic emission layer **370**, and the common electrode **270** are formed.

[0099] The pixel electrode **191** is an anode, which is a hole injection electrode, and the common electrode **270** is a cathode, which is an electron injection electrode. However, embodiments are not limited thereto, and the pixel electrode **191** may be a cathode, and the common electrode **270** may be an anode according to a driving method of the OLED display. When holes and electrons from the pixel electrode **191** and the common electrode **270**, respectively, are injected into the organic emission layer **370** and excitons in which the injected holes and electrons are coupled drop from an excited state to a ground state, light is emitted.

[0100] The organic emission layer **370** is made of a low polymer organic material or a high polymer organic material such as poly 3,4-ethylenedioxythiophene (PEDOT). Further, the organic emission layer **370** may be formed as a multilayer including at least one of an emission layer, a hole injection layer (HIL), a hole transporting layer (HTL), an electron transporting layer (ETL), and an electron injection layer

(EIL). When the multilayer includes all of the emission layer, the HIL, the HTL, the ETL, and the EIL, the HIL is disposed on the pixel electrode **191**, which is a positive electrode, and the HTL, the emission layer, the ETL, and the EIL are sequentially stacked thereon. The common electrode **270** is made of a reflective conductive material and becomes a rear light emitting OLED display. As a reflective material, a material such as lithium (Li), calcium (Ca), lithium fluoride/calcium (LiF/Ca), lithium fluoride/aluminum (LiF/Al), aluminum (Al), silver (Ag), magnesium (Mg), or gold (Au) may be used. **[0101]** While this disclosure has been described in connection with certain embodiments, it is to be understood that the invention is not limited to the disclosed embodiments, but, on the contrary, is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims.

<Description of symbols>	
110: substrate	121: scan line
122: previous scan line	123: light emission control line
124: initialization voltage line	125a: driving gate electrode
125b: switching gate electrode	126: first storage capacitor plate
127: second storage capacitor plate	128: first boosting capacitor plate
129: second boosting capacitor plate	131: semiconductor layer
141: first gate insulating layer	142: second gate insulating layer
160: interlayer insulating layer	171: data line
172: driving voltage line	174: connection member

- What is claimed is:
- 1.** An organic light emitting diode (OLED) display, comprising:
 - a substrate;
 - a scan line formed over the substrate configured to transfer a scan signal;
 - a data line that intersects the scan line and is configured to transfer a data signal
 - a driving voltage line that intersects the scan line and is configured to transfer a driving voltage;
 - a switching thin film transistor (TFT) connected to the scan line and the data line;
 - a driving TFT connected to the switching TFT and the driving voltage line, the driving TFT comprising a driving gate electrode;
 - an OLED connected to the driving TFT;
 - a storage capacitor connected between the driving voltage line and the driving gate electrode; and
 - a boosting capacitor connected to the storage capacitor, wherein the storage capacitor has at least one capacitor opening.
 - 2.** The OLED display of claim **1**, wherein the driving TFT further comprises
 - a driving semiconductor layer formed on the substrate, and wherein
 - the driving gate electrode is formed on a first gate insulating layer and a second gate insulating layer that sequentially cover the driving semiconductor layer, the driving gate electrode overlapped with the driving semiconductor layer.
 - 3.** The OLED display of claim **2**, wherein the storage capacitor comprises:
 - a first storage capacitor plate formed over the first gate insulating layer;

- a second gate insulating layer covering the first storage capacitor plate; and
 - a second storage capacitor plate formed over the second gate insulating layer and overlapped with the first storage capacitor plate.
- 4.** The OLED display of claim **3**, wherein the capacitor opening is formed in the second storage capacitor plate.
 - 5.** The OLED display of claim **4**, further comprising an interlayer insulating layer covering the second storage capacitor plate,
 - wherein the driving gate electrode is connected to the first storage capacitor plate through a contact hole positioned within the capacitor opening and formed in the interlayer insulating layer and the second gate insulating layer.
 - 6.** The OLED display of claim **5**, wherein the driving voltage line is formed over the interlayer insulating layer and is spaced apart from the capacitor opening.
 - 7.** The OLED display of claim **6**, wherein a first side separation terminal and a second side separation terminal of the driving voltage line are connected to the second storage capacitor plate through a first side contact hole and a second side contact hole, respectively, the first side and the second side contact holes formed in the interlayer insulating layer.
 - 8.** The OLED display of claim **7**, further comprising a connection member formed in the same layer, and configured to be parallel to, the driving voltage line, and further configured to connect the driving gate electrode and the first storage capacitor plate.
 - 9.** The OLED display of claim **8**, wherein a first end of the connection member is connected to the driving gate electrode through a contact hole formed in the interlayer insulating layer, and a first intermediate protruding portion of the connection member is connected to the first storage capacitor plate through a contact hole formed in the interlayer insulating layer and the second gate insulating layer.
 - 10.** The OLED display of claim **8**, further comprising an initialization TFT configured to be turned on according to a previous scan signal received through a previous scan line and further configured to transfer an initialization voltage to a driving gate electrode of the driving TFT,
 - wherein a second end of the connection member is connected to an initialization semiconductor layer of the initialization TFT through a contact hole formed in the interlayer insulating layer, the second gate insulating layer, and the first gate insulating layer.
 - 11.** The OLED display of claim **8**, further comprising a compensating TFT configured to compensate a threshold voltage of the driving TFT and connected to the driving TFT,
 - wherein a second intermediate protruding portion of the connection member is connected to a compensation semiconductor layer of the compensation TFT through a contact hole formed in the interlayer insulating layer, the second gate insulating layer, and the first gate insulating layer.
 - 12.** The OLED display of claim **8**, wherein the boosting capacitor comprises a first boosting capacitor plate extended from the first storage capacitor and a second boosting capacitor plate overlapped with the first boosting capacitor plate and protruded from the scan line.
 - 13.** The OLED display of claim **12**, wherein the scan line and the driving gate electrode are formed co-planar with the second storage capacitor plate.

14. The OLED display of claim 12, wherein the previous scan line is formed co-planar with the first storage capacitor plate.

15. The OLED display of claim 12, wherein the first storage capacitor plate is formed co-planar with the first boosting capacitor plate, and the second storage capacitor plate is formed co-planar with the second boosting capacitor plate.

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